

**SANYO**

No.4669

**2SJ337**

P-Channel MOS Silicon FET

Very High-Speed Switching Applications

**Features**

- Low ON resistance.
- Very high-speed switching.
- Low-voltage drive.

**Absolute Maximum Ratings at Ta = 25°C**

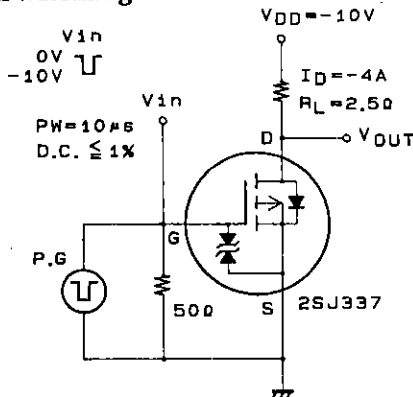
Parameter	Symbol	Value	unit
Drain-to-Source Voltage	V <sub>DSS</sub>	-12	V
Gate-to-Source Voltage	V <sub>GS</sub>	±18	V
Drain Current(DC)	I <sub>D</sub>	-8	A
Drain Current(Pulse)	I <sub>DP</sub>	-32	A
Allowable Power Dissipation	P <sub>D</sub>	1	W
	P <sub>D</sub>	30	W
Channel Temperature	T <sub>ch</sub>	150	°C
Storage Temperature	T <sub>stg</sub>	-55 to +150	°C

PW ≤ 10μs, duty cycle ≤ 1%  
Tc = 25°C

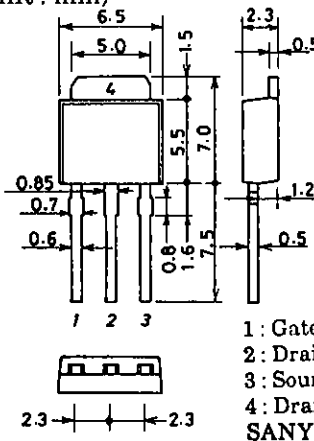
**Electrical Characteristics at Ta = 25°C**

Parameter	Symbol	Test Conditions	min	typ	max	unit
D-S Breakdown Voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> = -1mA, V <sub>GS</sub> = 0	-12			V
G-S Breakdown Voltage	V <sub>(BR)GSS</sub>	I <sub>G</sub> = ±100μA, V <sub>DS</sub> = 0	±18			V
Zero-Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = -12V, V <sub>GS</sub> = 0			-100	μA
Gate to Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = ±12V, V <sub>DS</sub> = 0			±10	μA
Cutoff Voltage	V <sub>GS(off)</sub>	V <sub>DS</sub> = -10V, I <sub>D</sub> = -1mA	-1.0		-2.0	V
Forward Transfer Admittance	Y <sub>fs</sub>	V <sub>DS</sub> = -10V, I <sub>D</sub> = -4A	4	6		S
Static Drain-to-Source ON-State Resistance	R <sub>DS(on)</sub>	I <sub>D</sub> = -4A, V <sub>GS</sub> = -10V		65	90	mΩ
	R <sub>DS(on)</sub>	I <sub>D</sub> = -4A, V <sub>GS</sub> = -4V		110	150	mΩ
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = -10V, f = 1MHz		1000		pF
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> = -10V, f = 1MHz		900		pF
Reverse Transfer Capacitance	C <sub>rss</sub>	V <sub>DS</sub> = -10V, f = 1MHz		220		pF
Turn-ON Delay Time	t <sub>d(on)</sub>	See specified Test Circuit.		15		ns
Rise Time	t <sub>r</sub>	"		50		ns
Turn-OFF Delay Time	t <sub>d(off)</sub>	"		220		ns
Fall Time	t <sub>f</sub>	"		145		ns
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> = -8A, V <sub>GS</sub> = 0	-1.0	-1.5		V

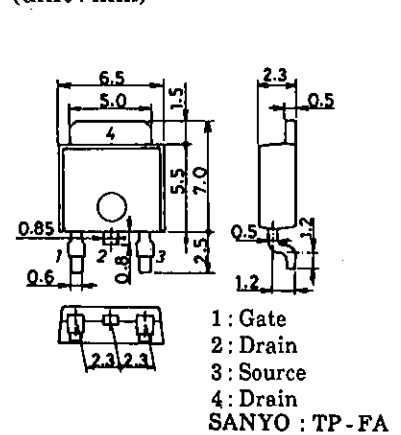
**Switching Time Test Circuit**

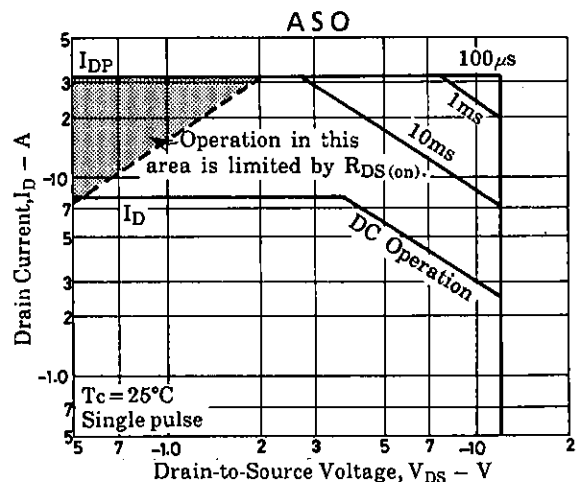
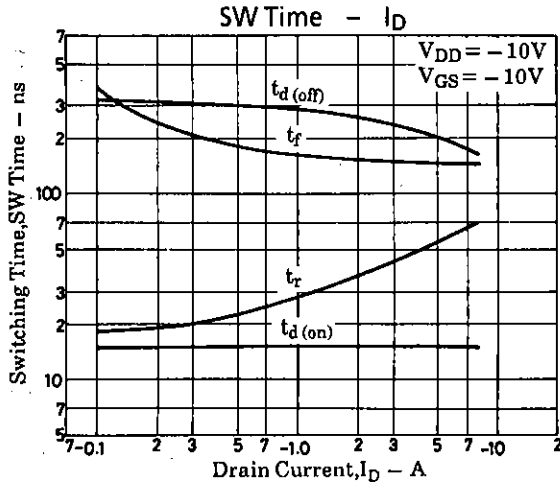
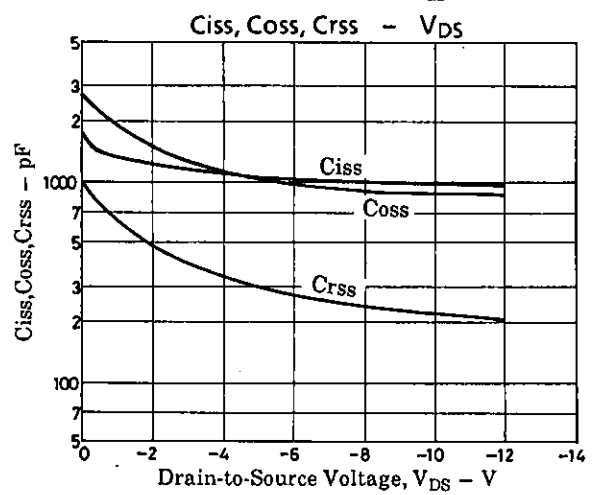
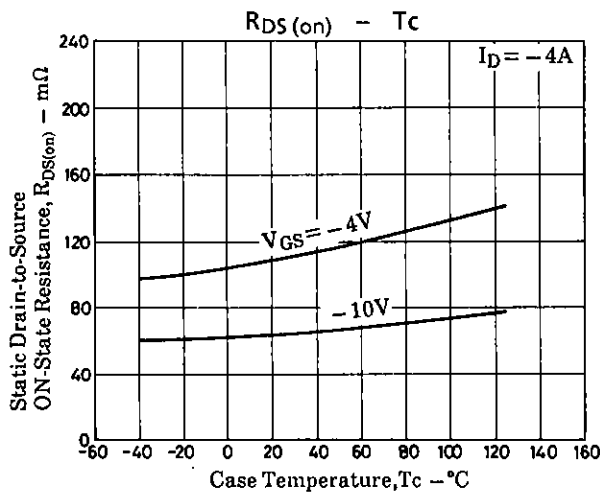
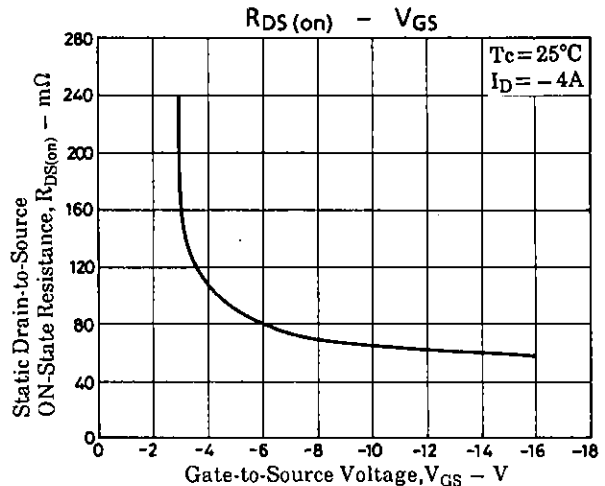
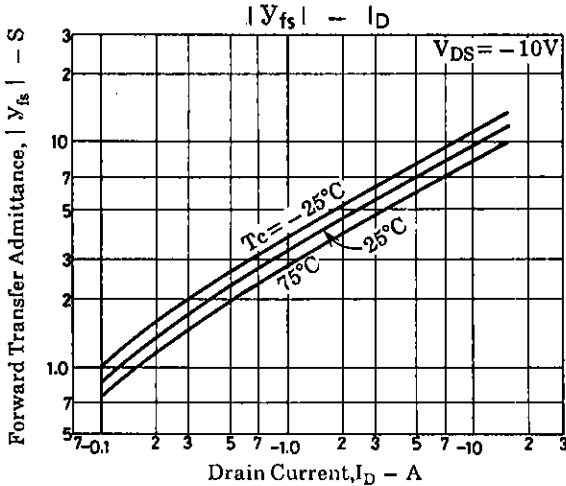
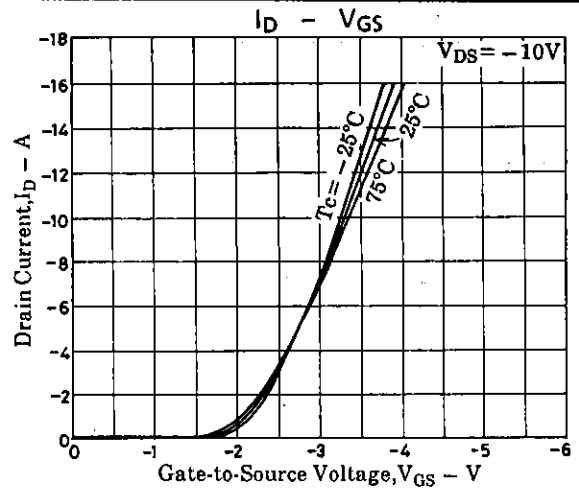
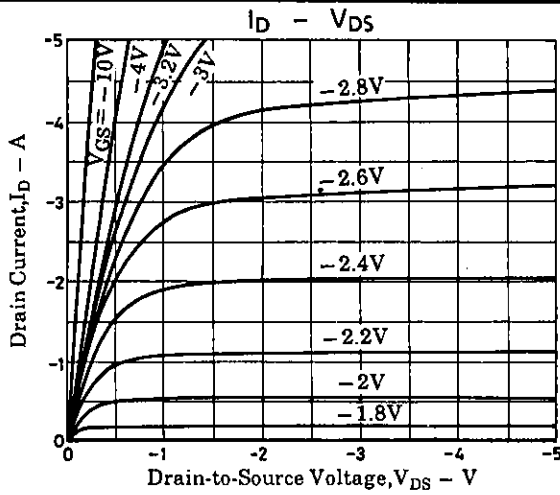


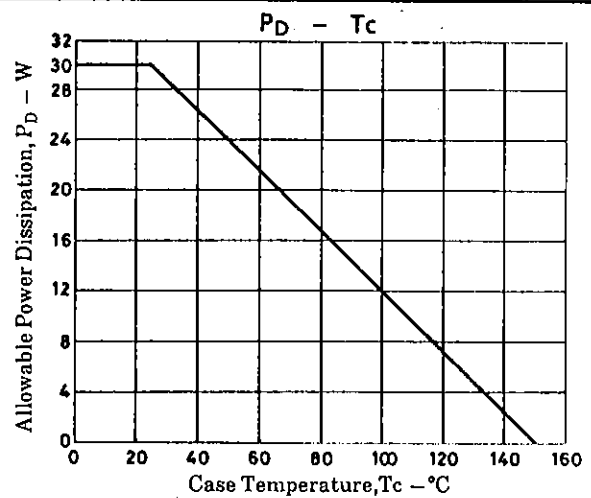
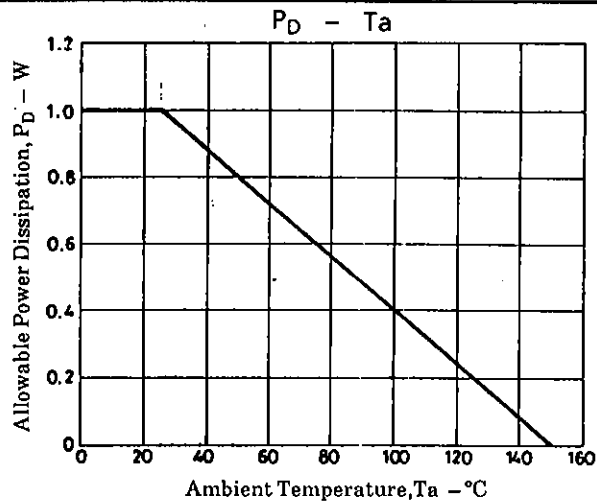
**Package Dimensions 2083B (unit : mm)**



**Package Dimensions 2092B (unit : mm)**







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